Quad Bus Buffer

with 3-State Control Inputs

The MC74VHCT125A is a high speed CMOS quad bus buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The MC74VHCT125A requires the 3–state control input (\overline{OE}) to be set High to place the output into the high impedance state.

The VHCT inputs are compatible with TTL levels. This device can be used as a level converter for interfacing 3.3V to 5.0V, because it has full 5V CMOS level output swings.

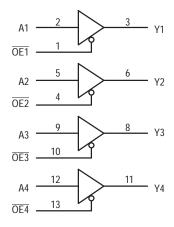
The VHCT125A input structures provide protection when voltages between 0V and 5.5V are applied, regardless of the supply voltage. The output structures also provide protection when $V_{CC} = 0V$. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7V, allowing the interface of 5V systems to 3V systems.

- High Speed: tpD = 3.8ns (Typ) at $V_{CC} = 5V$
- Low Power Dissipation: $I_{CC} = 4\mu A$ (Max) at $T_A = 25^{\circ}C$
- TTL-Compatible Inputs: V_{IL} = 0.8V; V_{IH} = 2.0V
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2V to 5.5V Operating Range
- Low Noise: VOLP = 0.8V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300mA
- ESD Performance: HBM > 2000V; Machine Model > 200V
- Chip Complexity: 72 FETs or 18 Equivalent Gates

LOGIC DIAGRAM

Active-Low Output Enables



FUNCTION TABLE

VHCT125A					
Inp	outs	Output			
Α	OE	Υ			
Н	L	Н			
L	L	L			
Х	Н	Z			



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14-LEAD SOIC D SUFFIX CASE 751A 14-LEAD TSSOP DT SUFFIX CASE 948G



14-LEAD SOIC EIAJ M SUFFIX CASE 965

PIN CONNECTION AND MARKING DIAGRAM (Top View)

OE1	1●	14	v _{CC}
A1 [2	13	OE4
Y1 🛭	3	12	D A4
OE2	4	11] Y4
A2 [5	10	OE3
Y2 [6	9] A3
GND [7	8] Y3

For detailed package marking information, see the Marking Diagram section on page 4 of this data sheet.

ORDERING INFORMATION

Device	Package	Shipping	
MC74VHCT125AD	SOIC	55 Units/Rail	
MC74VHCT125ADT	TSSOP	96 Units/Rail	
MC74VHCT125AM	SOIC EIAJ	50 Units/Rail	

MAXIMUM RATINGS*

Symbol	Parameter		Value	Unit
VCC	DC Supply Voltage		- 0.5 to + 7.0	V
V _{in}	DC Input Voltage		- 0.5 to + 7.0	V
V _{out}	DC Output Voltage		-0.5 to $V_{CC} + 0.5$	V
ΙΙΚ	Input Diode Current		– 20	mA
lok	Output Diode Current		± 20	mA
l _{out}	DC Output Current, per Pin		± 25	mA
ICC	DC Supply Current, V_{CC} and GND Pin	S	± 50	mA
PD		IC Packages† OP Package†	500 450	mW
T _{stg}	Storage Temperature		- 65 to + 150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq VCC. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or VCC).

Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
VCC	DC Supply Voltage	4.5	5.5	V
Vin	DC Input Voltage	0	5.5	V
V _{out}	DC Output Voltage	0	Vcc	V
TA	Operating Temperature, All Package Types	- 40	+ 85	°C
t _r , t _f	Input Rise and Fall Time $V_{CC} = 5.0V \pm 0.5V$	0	20	ns/V

DC ELECTRICAL CHARACTERISTICS

			V_{CC} $T_A = 25^{\circ}C$ $T_A \le 85^{\circ}C$ T_A		T _A = 25°C		T _A ≤ '	125°C			
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
VIH	Minimum High–Level Input Voltage		3.0 4.5 5.5	1.2 2.0 2.0			1.2 2.0 2.0		1.2 2.0 2.0		V
VIL	Maximum Low–Level Input Voltage		3.0 4.5 5.5			0.53 0.8 0.8		0.53 0.8 0.8		0.53 0.8 0.8	V
VOH	Minimum High-Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OH} = - 50μA	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		V
	VIN = VIH or VIL	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4\text{mA}$ $I_{OH} = -8\text{mA}$	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
VOL	Maximum Low–Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OL} = 50μA	3.0 4.5		0.0 0.0	0.1 0.1		0.1 0.1		0.1 0.1	V
	VIN = VIH or VIL	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4\text{mA}$ $I_{OL} = 8\text{mA}$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I _{IN}	Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			± 0.1		± 1.0		± 1.0	μΑ
lcc	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			2.0		20		40	μΑ
ICCT	Quiescent Supply Current	Input: V _{IN} = 3.4V	5.5			1.35		1.50		1.65	mA
IOPD	Output Leakage Current	V _{OUT} = 5.5V	0.0			0.5		5.0		10	μΑ

^{*} Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute—maximum—rated conditions is not implied.

[†]Derating — SOIC Packages: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

AC ELECTRICAL CHARACTERISTICS (Input $t_{\Gamma} = t_f = 3.0 \text{ns}$)

			1	Γ _A = 25°	С	T _A = ≤ 85°C		T _A ≤ 125°C		
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Min	Max	Unit
tPLH, tPHL	Maximum Propagation Delay, A to Y	$V_{CC} = 3.3 \pm 0.3 V C_{L} = 15 pF$ $C_{L} = 50 pF$		5.6 8.1	8.0 11.5	1.0 1.0	9.5 13.0		12.0 16.0	ns
		$V_{CC} = 5.0 \pm 0.5 V C_L = 15 pF$ $C_L = 50 pF$		3.8 5.3	5.5 7.5	1.0 1.0	6.5 8.5		8.5 10.5	
t _{PZL} , t _{PZH}	Maximum Output Enable TIme, OE to Y	$\begin{array}{c} \text{V}_{\text{CC}} = 3.3 \pm 0.3 \text{V C}_{\text{L}} = 15 \text{pF} \\ \text{R}_{\text{L}} = 1 \text{k} \Omega & \text{C}_{\text{L}} = 50 \text{pF} \end{array}$		5.4 7.9	8.0 11.5	1.0 1.0	9.5 13.0		11.5 15.0	ns
		$V_{CC} = 5.0 \pm 0.5 V C_L = 15 pF$ $R_L = 1 k\Omega$ $C_L = 50 pF$		3.6 5.1	5.1 7.1	1.0 1.0	6.0 8.0		7.5 9.5	
t _{PLZ} , t _{PHZ}	Maximum Output Disable Time, OE to Y	$V_{CC} = 3.3 \pm 0.3 V C_{L} = 50 pF$ $R_{L} = 1 k\Omega$		9.5	13.2	1.0	15.0		18.0	ns
		$V_{CC} = 5.0 \pm 0.5 V C_L = 50 pF$ $R_L = 1 k\Omega$		6.1	8.8	1.0	10.0		12.0	
tOSLH, tOSHL	Output-to-Output Skew	V _{CC} = 3.3 ± 0.3V C _L = 50pF (Note 1.)			1.5		1.5		2.0	ns
		V _{CC} = 5.0 ± 0.5V C _L = 50pF (Note 1.)			1.0		1.0		1.5	
C _{in}	Maximum Input Capacitance			4	10		10		10	pF
C _{out}	Maximum Three–State Output Capacitance (Output in High Impedance State)			6						pF

		Typical @ 25°C, V _{CC} = 5.0V	
C _{PD}	Power Dissipation Capacitance (Note 2.)	14	pF

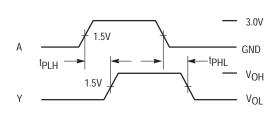
^{1.} Parameter guaranteed by design. $t_{OSLH} = |t_{PLHm} - t_{PLHn}|$, $t_{OSHL} = |t_{PHLm} - t_{PHLn}|$.

$\textbf{NOISE CHARACTERISTICS} \; (\text{Input } t_f = t_f = 3.0 \text{ns}, \; C_L = 50 \text{pF}, \; \forall_{CC} = 5.0 \text{V})$

			25°C	
Symbol	Characteristic	Тур	Max	Unit
VOLP	Quiet Output Maximum Dynamic VOL	0.3	0.8	V
VOLV	Quiet Output Minimum Dynamic V _{OL}	- 0.3	- 0.8	V
VIHD	Minimum High Level Dynamic Input Voltage		3.5	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

^{2.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/4 (per buffer). C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

SWITCHING WAVEFORMS



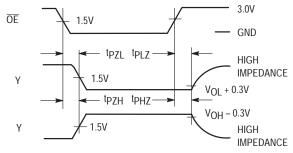
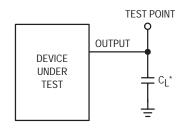
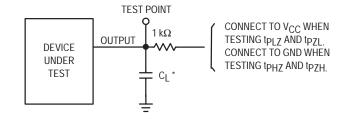


Figure 1.

Figure 2.





*Includes all probe and jig capacitance

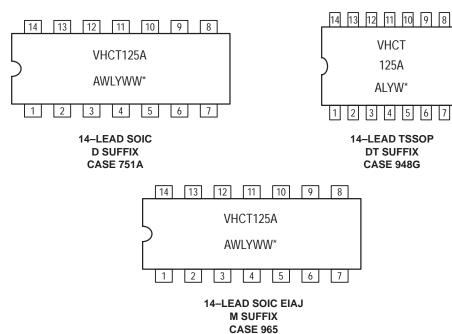
Figure 3. Test Circuit

*Includes all probe and jig capacitance

Figure 4. Test Circuit

MARKING DIAGRAMS

(Top View)

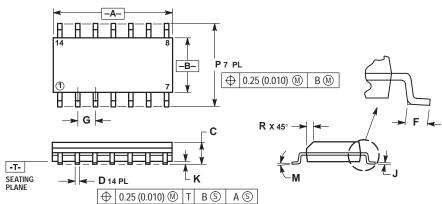


*See Applications Note #AND8004/D for date code and traceability information.

PACKAGE DIMENSIONS

D SUFFIX PLASTIC SOIC PACKAGE

CASE 751A-03 ISSUE F



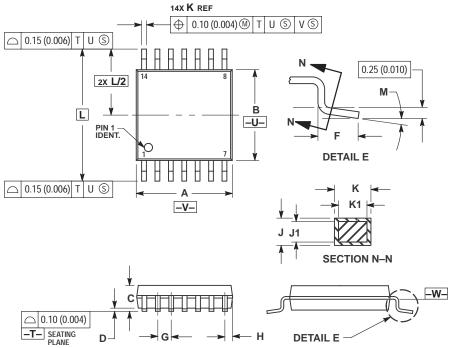
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	8.55	8.75	0.337	0.344	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
P	5.80	6.20	0.228	0.244	
R	0.25	0.50	0.010	0.019	

PACKAGE DIMENSIONS

DT SUFFIX

PLASTIC TSSOP PACKAGE CASE 948G-01 ISSUE O



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15

 (0.006) PER SIDE.
- ON ON THE BORNS STRIKE HOT EXCELS O.T.)

 O(0.006) PER SIDE.

 DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED

 0.25 (0.010) PER SIDE.

 DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

 TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

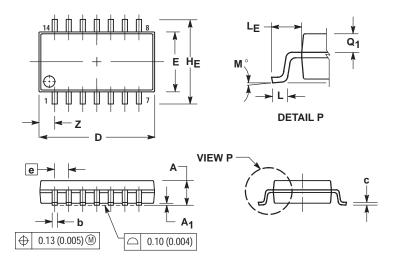
 DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE —W.—
- AT DATUM PLANE -W-.

	MILLIN	METERS	TERS INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40		0.252 BSC		
M	0°	8°	0°	8°	

PACKAGE DIMENSIONS

M SUFFIX

PLASTIC SOIC EIAJ PACKAGE CASE 965-01 ISSUE O



NOTES:

- OTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSIONS ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	METERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α		2.05		0.081	
A ₁	0.05	0.20	0.002	0.008	
b	0.35	0.50	0.014	0.020	
С	0.18	0.27	0.007	0.011	
D	9.90	10.50	0.390	0.413	
Ε	5.10	5.45	0.201	0.215	
е	1.27	BSC	0.050 BSC		
ΗE	7.40	8.20	0.291	0.323	
0.50	0.50	0.85	0.020	0.033	
LE	1.10	1.50	0.043	0.059	
M	0 °	10 °	0 °	10°	
Q ₁	0.70	0.90	0.028	0.035	
7		1 42		0.056	

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